

isc Silicon NPN Power Transistor

2SD732

DESCRIPTION

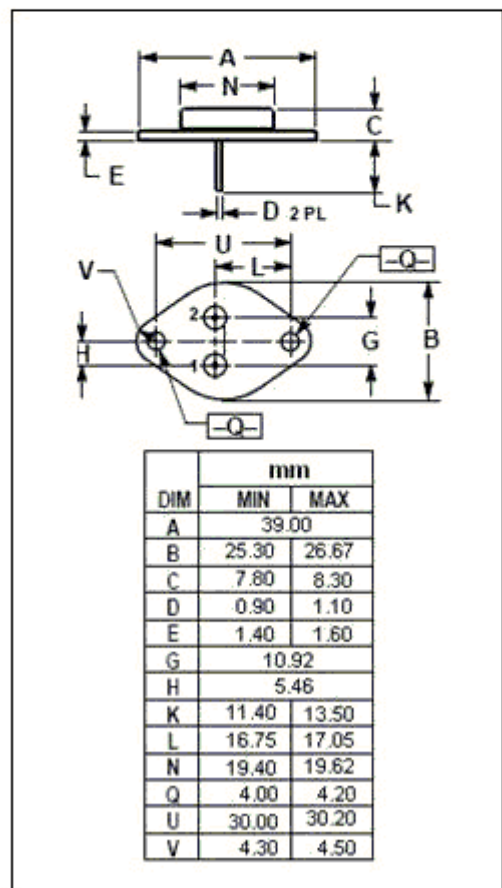
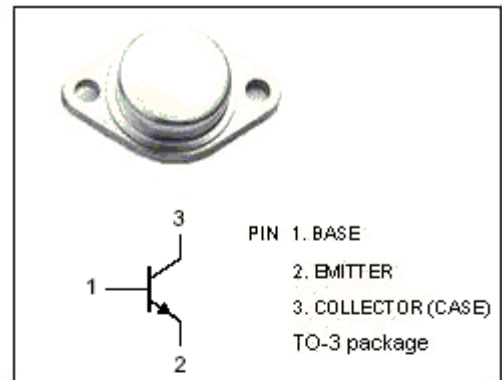
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 120V$  (Min)
- High Current Capability
- Complement to Type 2SB696

APPLICATIONS

- Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-Peak	12	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-40~150	$^{\circ}C$



**isc Silicon NPN Power Transistor****2SD732****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; R_{BE}=\infty$	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$		0.6		V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}; V_{CE}=5\text{V}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			0.1	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	40		320	
$f_T$	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=5\text{V}$		15		MHz

◆  **$h_{FE}$  Classifications**

C	D	E	F
40-80	60-120	100-200	160-320